

# mPD166036GR

## INTELLIGENT POWER DEVICE

R07DS1118EJ0200 Rev.2.00 Aug 01, 2014

## **Description**

The mPD166036 is an N-channel high side driver with built-in charge pump and embedded protection function. It is also a linear solenoid driver with a built-in differential amplifier.

When device is overtemperature or overcurrent is generated in output MOS, the protection function operates to prevent destruction and degradation of the product. When the current flows through the external shunt resistor near the input part of the differential amplifier, the voltage drops at each end of the resistor. The output current can be monitored when the microcomputer reads the output voltage from the amplifier.

#### **Features**

- High temperature operation ( $T_{ch} = 175^{\circ}C \text{ MAX.}$ )
- · Built-in charge pump circuit
- · Low on-state resistance

 $R_{DS(ON)} = 100 \text{ mWMAX.} (V_{IN} = V_{IH}, I_O = 1.5A, T_{ch} = 25^{\circ}\text{C})$ 

- · Built-in protection circuit
  - 3/4 Current limitation
  - 3/4 Overtemperature protection
- Built-in differential amplifier (gain = 8 times)
- · Package: Power SOP 8

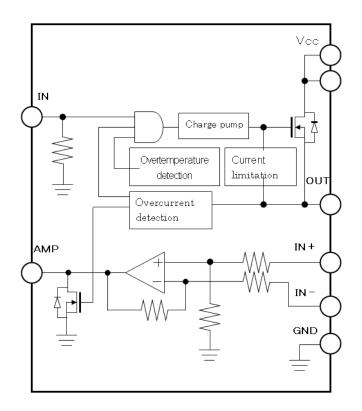
### **Application**

· Switching of all types of 14 V DC grounded loads, such as inductor, resistor and capacitor

### **Ordering Information**

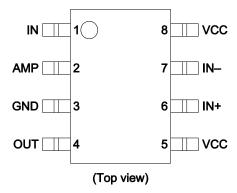
| Part No.          | Lead Plating | Packing          | Package     |  |
|-------------------|--------------|------------------|-------------|--|
| mPD166036GR-E1-AY | Sn           | Tape 2500 p/reel | Power SOP 8 |  |
| mPD166036GR-E2-AY | Sn           | Tape 2500 p/reel | Power SOP 8 |  |

# **Block Diagram**



# **Pin Configuration**

· Power SOP 8



## **Pin Functions**

| Pin No. | Pin Name | Function                           |  |  |
|---------|----------|------------------------------------|--|--|
| 1       | IN       | Input pin                          |  |  |
| 2       | AMP      | Differential amplifier output pin  |  |  |
| 3       | GND      | Ground pin                         |  |  |
| 4       | OUT      | High side output pin               |  |  |
| 5       | VCC      | Power supply pin                   |  |  |
| 6       | IN+      | Differential amplifier + input pin |  |  |
| 7       | IN-      | Differential amplifier – input pin |  |  |
| 8       | VCC      | Power supply pin                   |  |  |

# **Absolute Maximum Ratings**

 $(Ta = 25^{\circ}C, unless otherwise specified)$ 

| Item                           | Symbol                   | Rating              | Unit | Condition   |
|--------------------------------|--------------------------|---------------------|------|---|
| Power supply voltage           | V <sub>CC1</sub>         | -0.3 to +28         | V    |   |
|                                | V <sub>CC2</sub>         | 35                  | V    | t = 300 ms  |
| IN input voltage               | V <sub>IN1</sub>         | -0.5 to +5.5        | V    | IN pin  |
|                                | V <sub>IN2</sub>         | 5                   | V    | $V_{CC} = 0 \text{ V}, t = 0.5 \text{ s}, IN pin$ |
| IN input current               | I <sub>IN</sub>          | ±10                 | mA   |   |
| Amplifier input voltage        | $V_{IN_{\underline{+}}}$ | -0.5 to +5.5        | V    | IN+/IN- pin                                       |
| Amplifier input current        | I <sub>IN±</sub>         | ±10                 | mA   | IN pin, IN+/IN- pin                               |
| Output current                 | I <sub>OA</sub>          | 2                   | А    |   |
| Output negative voltage        | V <sub>OA</sub>          | V <sub>CC</sub> -40 | V    |   |
| Power dissipation              | P <sub>D</sub>           | 1.91                | W    | T <sub>a</sub> = 25°C Note                        |
| Operation temperature          | T <sub>OPT</sub>         | -40 to +125         | °C   |   |
| Storage temperature            | T <sub>STG</sub>         | -55 to +175         | °C   |   |
| Current monitor output voltage | V <sub>AMP</sub>         | 7.0                 | V    |   |
| Current monitor output current | I <sub>AMP</sub>         | 10                  | mA   |   |

Note: When mounted on a epoxy PCB (where FR-4 is 10 cm ´ 10 cm, dimension of copper foil is 15% and thickness of copper foil is 35 mm), PW = 10 s

## **Electrical Characteristics**

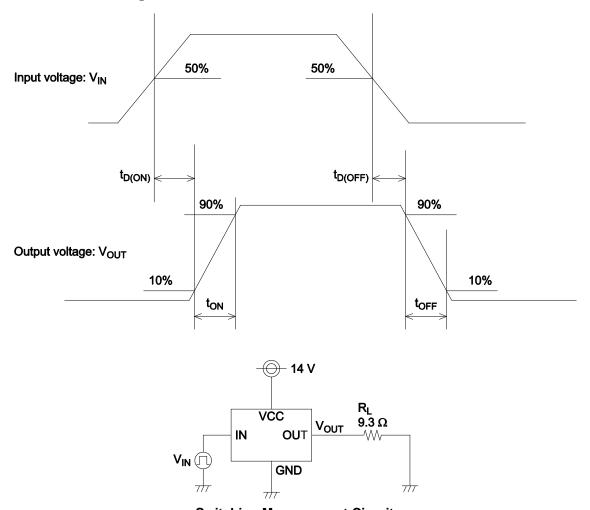
( $V_{CC}$  = 8 to 16 V,  $T_{ch}$  = -40 to +175°C, unless otherwise specified)

| li                        | tem                         | Symbol                        | MIN.  | TYP.   | MAX. | Unit  | it Condition  |                           |
|---------------------------|-----------------------------|-------------------------------|-------|--|------|-------|---|---------------------------|
| Input volta               | ge                          | V <sub>IH</sub>               | 2.8   | _  | 5.5  | V     | V <sub>CC</sub> = 4.5 to 16 V                                       |                           |
|                           |                             | V <sub>IL</sub>               | 0     | _  | 1.5  | V     |   |                           |
| Input curre               | nt                          | I <sub>IH</sub>               | -     | _  | 350  | mA    | V <sub>IN</sub> = 5.5 V   |                           |
|                           |                             | I <sub>IL</sub>               | -10   | _  | _    | mΑ    | $V_{IN} = 0 V$  |                           |
| Standby cu                | urrent                      | Іссн                          | _     | _  | 4    | mA    | V <sub>IN</sub> = V <sub>IH</sub> or V <sub>IL</sub> Note 1         |                           |
| Output lea                | kage current                | I <sub>OL</sub>               | -0.24 | _  | _    | mA    | $V_{IN} = V_{IL}, V_O = 0 V$  |                           |
| Drain to so               | urce on-state               | R <sub>DS(ON)</sub>           | _     | _  | 100  | mW    | $V_{IN} = V_{IH}, I_O = 1.5 A$                                      | T <sub>ch</sub> = 25°C    |
| resistance                |                             |                               | _     | _  | 180  | mW    |   | T <sub>ch</sub> = 150°C   |
| Overcurrer                | nt detection                | Is                            | 2     | _  | 10   | Α     |   |                           |
| Overtempe<br>detection    | erature                     | T <sub>th</sub>               | (175) | _  | _    | °C    | Note 2  |                           |
| Turn on de                | lay time                    | t <sub>D(ON)</sub>            | _     | 2  | 200  | ms    | $R_L = 9.3 \text{ W}, V_{CC} = 14 \text{ V},$                       |                           |
| Turn off de               | lay time                    | t <sub>D(OFF)</sub>           |       | 20   | 200  | ms    | $V_{IN} = 5 V - 0 V$  |                           |
| Rise time                 |                             | t <sub>ON</sub>               |       | 19   | 100  | ms    |   |                           |
| Fall time                 |                             | t <sub>OFF</sub>              | _     | 4  | 100  | ms    |   |                           |
| Negative o                | utput current               | -l <sub>0</sub>               | _     | _  | 15   | mA    | V <sub>cc</sub> -V <sub>out</sub> =40V                              |                           |
| At over current condition | Output oscillation cycle    | ts                            | _     | _  | 14   | ms    | Overcurrent   |                           |
|                           | Output on duty              | Ds                            | _     | _  | 30   | %     | Overcurrent   |                           |
|                           | Abnormal low level voltage  | V <sub>ADG</sub>              | _     | _  | 0.08 | V     | Overcurrent detection I <sub>OAMP</sub> = 0.1mA                     |                           |
| Amplifier o range         | utput voltage               | VOAMP                         | 0     | _  | 7.0  | V     | RL <sub>AMP</sub> = 50 kW (connect to ground)                       |                           |
| Amplifier o               | utput current               | I <sub>OAMP</sub><br>(SOURCE) | _     | _  | -0.1 | mA    | $R_{sh} = 0.25 \text{ W}, I_{sh} = 1.50 \text{ A}, V_{OAMP}  0.977$ |                           |
|                           | I <sub>OAMP</sub> 0.1 — — I |                               | mA    | $R_{sh} = 0.25 \text{ W}, I_{sh} = 1.50 \text{ A}, V_{OAMP} \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \$ |      |       |   |                           |
| Amplifier slew rate SF    |                             | SR <sub>CM</sub>              | _     | 0.9  | _    | V/ms  | RL <sub>AMP</sub> = 50 kW (connect to ground)                       |                           |
| Amplifier gain            |                             | GAIN                          | _     | 8  | _    | Times |   |                           |
| Current detection         |                             | V <sub>OGAINW(0.05)</sub>     | -47.0 | _  | 47.0 | %     | R <sub>sh</sub> = 0.25 W  | $I_{sh} = 0.05 A$         |
| accuracy                  |                             | V <sub>OGAINW(0.10)</sub>     | -23.8 | _  | 23.8 | %     | $RL_{AMP} = 50 \text{ kW}$  | $I_{sh} = 0.10 \text{ A}$ |
|                           |                             | V <sub>OGAINW(0.15)</sub>     | -16.0 | _  | 16.0 | %     | (connect to ground)   | I <sub>sh</sub> = 0.15 A  |
|                           |                             | V <sub>OGAINW(0.50)</sub>     | -5.4  | _  | 5.4  | %     |   | $I_{sh} = 0.50 \text{ A}$ |
|                           |                             |                               | -3.1  | _  | 3.1  | %     |   | I <sub>sh</sub> = 1.00 A  |
|                           |                             | V <sub>OGAINW(1.50)</sub>     | -2.3  |  | 2.3  | %     |   | I <sub>sh</sub> = 1.50 A  |

Notes: 1. OUT current is not included.

2. Not subject to production test, specified by design.

# **Definition of Switching Time**



**Switching Measurement Circuit** 

## **Truth Table**

| Item                      | V <sub>IN</sub> | V <sub>OUT</sub> | V <sub>AMP</sub> |
|---------------------------|-----------------|------------------|------------------|
| Normal operation          | Н               | Н                | AMP              |
|                           | L               | L                | AMP              |
| Overtemperature detection | Н               | L                | AMP              |
|                           | L               | L                | AMP              |
| Overcurrent detection     | Н               | Chopping         | L                |
|                           | L               | L                | L                |

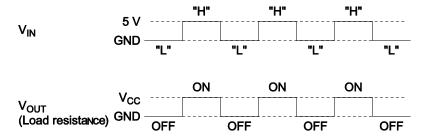
#### **Outline of Functions**

#### Pre-Driver (Charge Pump Circuit) ON/OFF Control

When the input voltage of the input pin (IN) is high level (2.8 V or more), the output MOS (Nch) turns on.

When the output voltage of the input pin (IN) is low level (1.5 V or less), the output MOS (Nch) turns off.

Charge pump circuit is built-in to drive the output MOS (Nch) that is connected to the high side.



#### **Overcurrent Detection Circuit**

This circuit detects overcurrent to output pin (OUT) caused by short circuit etc., and feeds back detection signal to control circuit.

When the overcurrent is detected, the current limitation circuit and the control circuit start operation. The output current is restricted and chopping operation begins.

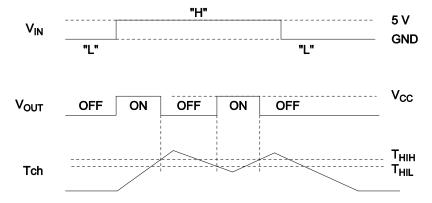
#### **Current Limitation Circuit**

This circuit limits the output current by using the detection signal from the overcurrent detection circuit, preventing destruction and degradation of the product.

#### **Overtemperature Detection Circuit**

This circuit detects overtemperature by output MOS (Nch) driving, and feeds back detection signal to control circuit.

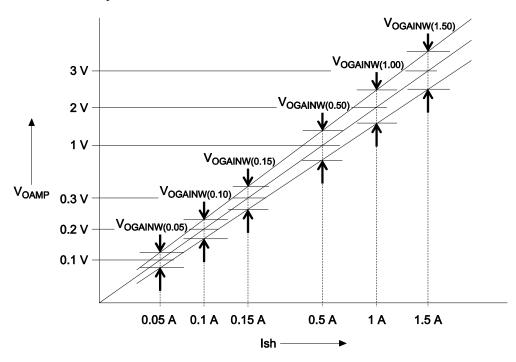
When the circuit detects overtemperature, the protection function of the control circuit operates and output is shutdown. Output MOS (Nch) automatically restarts when channel temperature cools down after shutdown.

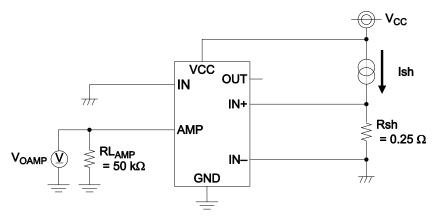


### **Differential Amplifier Circuit**

This amplifier circuit amplifies the differential input voltage (IN+ and IN-) to the differential amplifier eight times. When the current flows through the external shunt resistor ( $R_{sh}$ ) near the input part of the differential amplifier, the voltage drops at each end of the resistor. The output current can be monitored when the A/D converter in the microcomputer reads the output voltage from the amplifier.

The linear solenoid driver monitors the current through the differential amplifier circuit, and drives constant current by controlling the PWM of the output MOS.

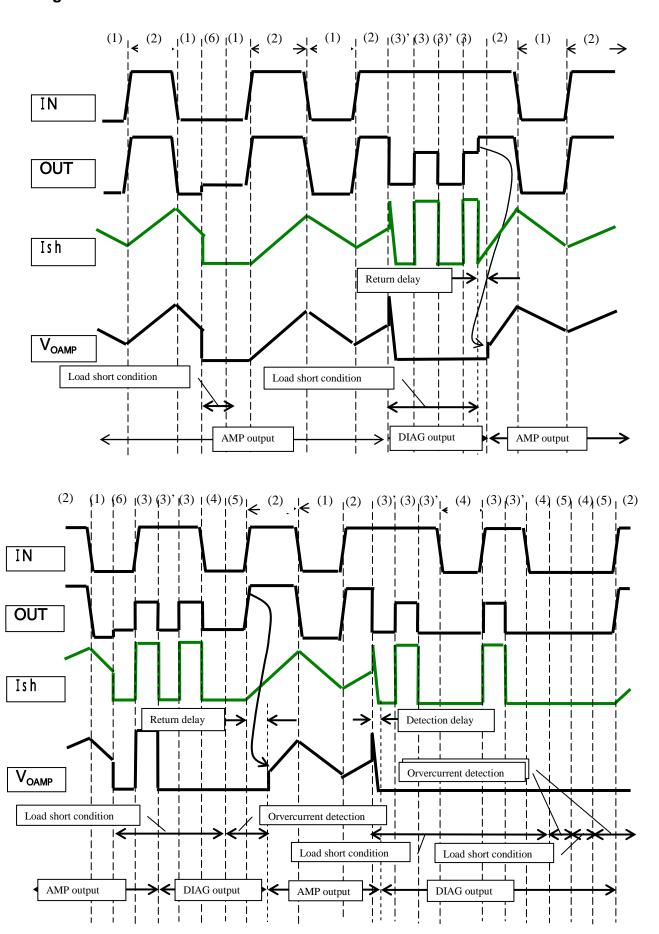


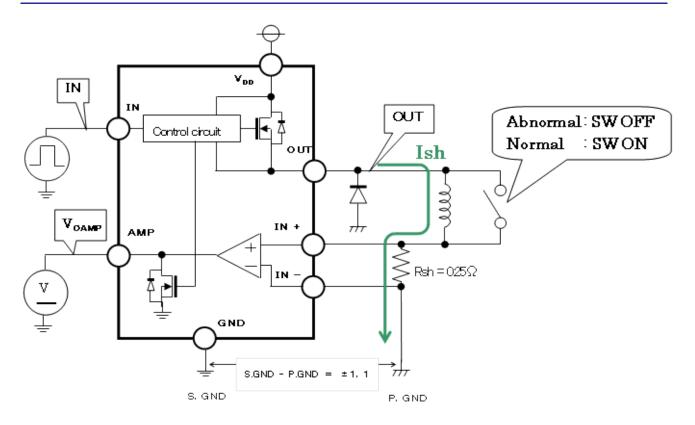


**Amplifier Characteristic Measurement Circuit** 

#### State transition diagram Input: Low Input: High Io = normal Input: High Status : ® $\mathbf{Status}: \textcircled{1}$ $\mathsf{Status} : \mathbb{2}$ I Output : OFF Output : OFF Output : ON Io = normal Load state : Abnormal Load state : normal Load state : normal Time out AMP output state: AMP AMP output state: AMP AMP output state: AMP Input: Low Io = overload Io = overload Status : ③ Output: OFF Load state : Abnormal AMP output state: L Input: Low Input: High lo = normal Time out Input: Low Status : ⑤ Status : ④ Status : ③ Output: OFF Output: OFF Output: ON Load state : Abnormal Load state : Abnormal Load state : Abnormal AMP output state: L AMP output state: L AMP output state: L lo = overload Input: High Abnormal Chopping Input: High state state

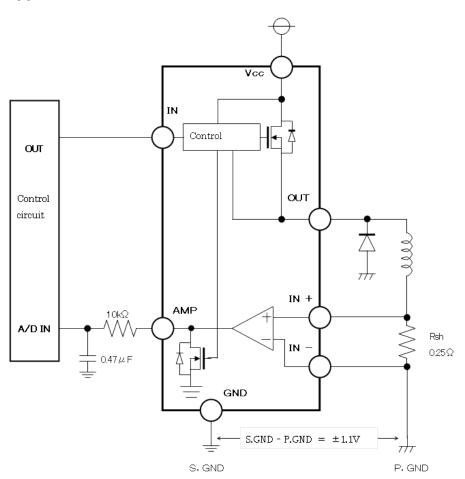
## **Timing Chart**



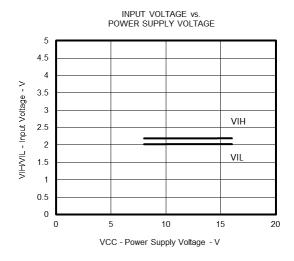


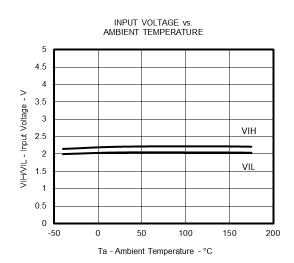
**Timing Chart Measurement Circuit** 

# **Example of Application Circuit**

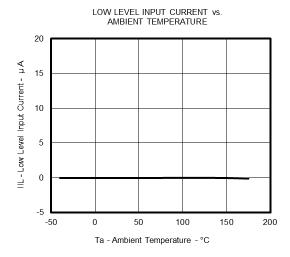


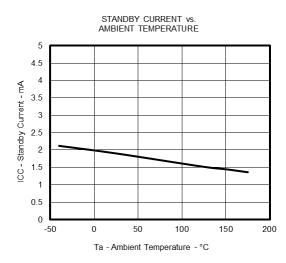
## **Typical Characteristics**

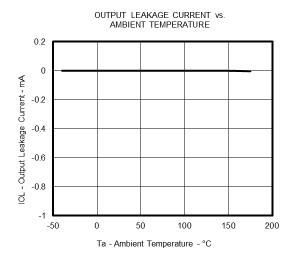


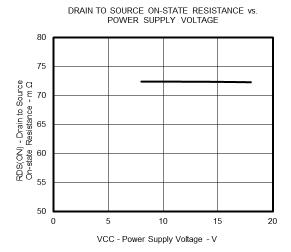


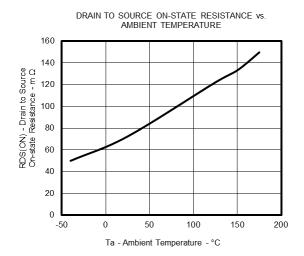


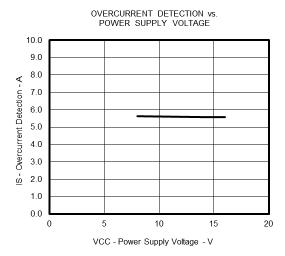


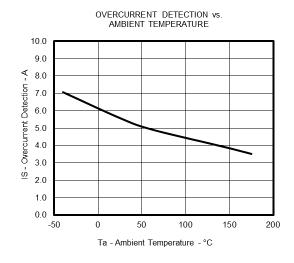


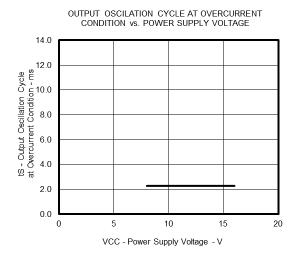


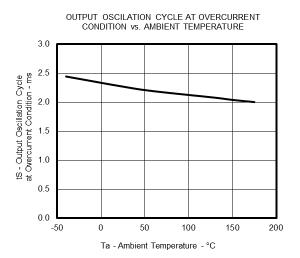


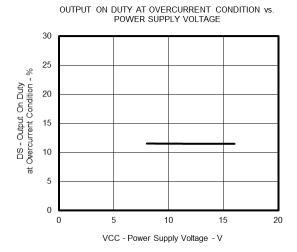


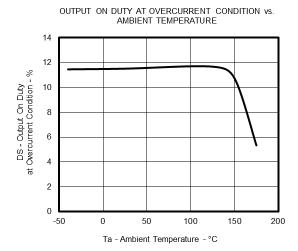


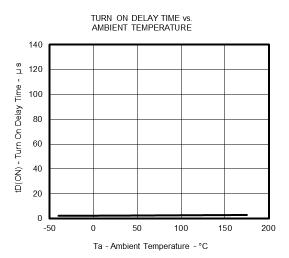


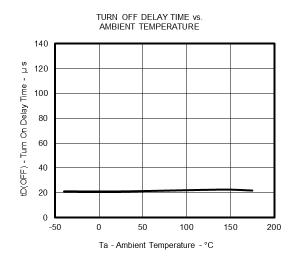


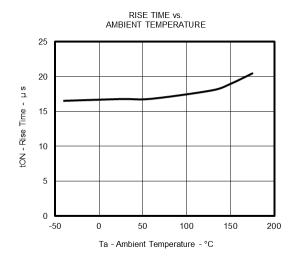


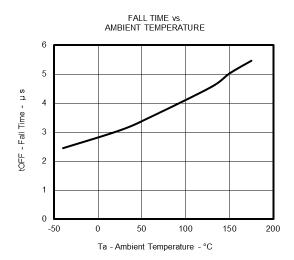


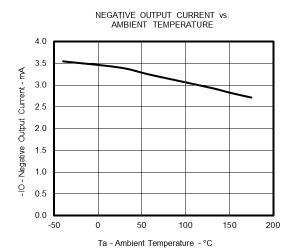


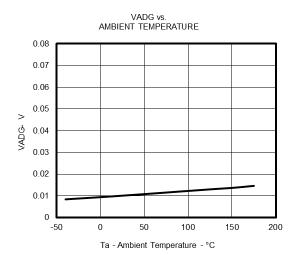


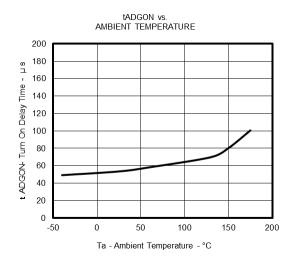


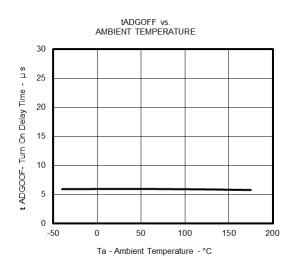


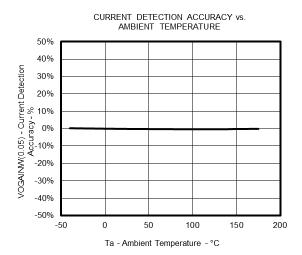


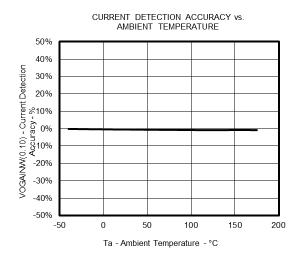


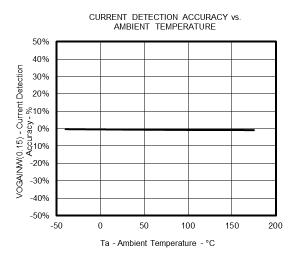


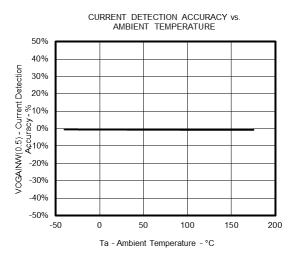


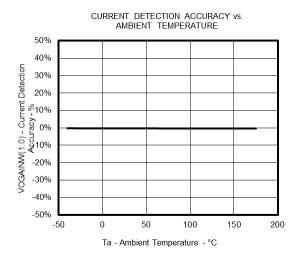


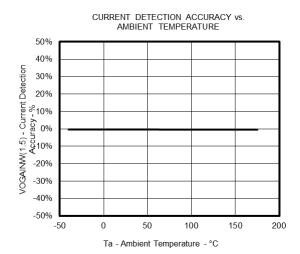




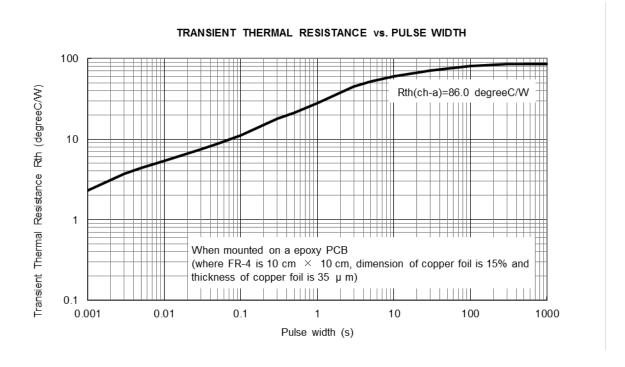




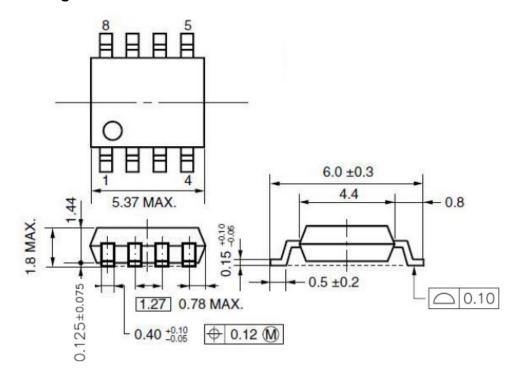




## **Transient Thermal Resistance Characteristics**

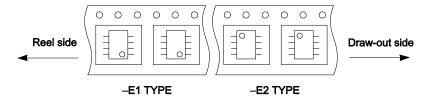


## **Package Drawing**



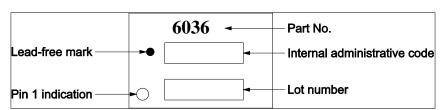
# **Taping Information**

There are two types (-E1, -E2) of taping depending on the direction of the device.



## **Marking Information**

This figure indicates the marking items and arrangement. However, details of the letterform, the size and the position aren't indicated.



## **Recommended Soldering Conditions**

The mPD166036 should be soldered and mounted under the following recommended conditions.

For soldering methods and conditions other than those recommended below, contact a Renesas Electronics sales representative.

For technical information, see the following website.

Semiconductor Package Mount Manual (http://www.renesas.com/products/package/manual/index.jsp)

- mPD166036GR-E1-AY Note: Power SOP 8
- mPD166036GR-E2-AY Note: Power SOP 8

| Process         | Conditions  | Symbol    |  |  |
|-----------------|---|-----------|--|--|
| Infrared reflow | Maximum temperature (package's surface temperature): 260°C or below,      | IR60-00-3 |  |  |
|                 | Time at maximum temperature: 10 seconds or less,                          |           |  |  |
|                 | Time at temperature higher than 220°C: 60 seconds or less,                |           |  |  |
|                 | Preheating time at 160°C to 180°C: 60 to 120 seconds, Times: Three times, |           |  |  |
|                 | Flux: Rosin flux with low chlorine (0.2 Wt% or below) recommended.        |           |  |  |
| Partial Heating | Pin temperature: 300°C or below,  | _         |  |  |
| Method          | Heat time: 3 seconds or less (Per each side of the device),               |           |  |  |
|                 | Flux: Rosin flux with low chlorine (0.2 Wt% or below) recommended.        |           |  |  |

Note: Pb-free (This product does not contain Pb in the external electrode.)

**Revision History** 

# mPD166036GR Data Sheet

|      |              | Description |   |  |
|------|--------------|-------------|---|--|
| Rev. | Date         | Page        | Summary   |  |
| 1.00 | Sep 20, 2013 | _           | First Edition Issued  |  |
| 2.00 | Aug 01, 2014 | 3           | 3 Absolute Maximum Ratings: IN input voltage(V <sub>IN1</sub> )<br>Change "-0.5V to +5.6V" to "-0.5V to +5.5V". |  |
|      |              | 18          | Semiconductor Package Mount Manual: Change URL.   |  |

#### **Notice**

- 1. Descriptions of circuits, software and other related information in this document are provided only to illustrate the operation of semiconductor products and application examples. You are fully responsible for the incorporation of these circuits, software, and information in the design of your equipment. Renesas Electronics assumes no responsibility for any losses incurred by you or third parties arising from the use of these circuits, software, or information.
- 2. Renesas Electronics has used reasonable care in preparing the information included in this document, but Renesas Electronics does not warrant that such information is error free. Renesas Electronics assumes no liability whatsoever for any damages incurred by you resulting from errors in or omissions from the information included herein
- 3. Renesas Electronics does not assume any liability for infringement of patents, copyrights, or other intellectual property rights of third parties by or arising from the use of Renesas Electronics products or technical information described in this document. No license, express, implied or otherwise, is granted hereby under any patents, copyrights or other intellectual property rights of Renesas Electronics or
- 4. You should not alter, modify, copy, or otherwise misappropriate any Renesas Electronics product, whether in whole or in part. Renesas Electronics assumes no responsibility for any losses incurred by you or third parties arising from such alteration, modification, copy or otherwise misappropriation of Renesas Electronics product.
- 5. Renesas Electronics products are classified according to the following two quality grades: "Standard" and "High Quality". The recommended applications for each Renesas Electronics product depends on the product's quality grade, as indicated below

"Standard": Computers; office equipment; communications equipment; test and measurement equipment; audio and visual equipment; home electronic appliances; machine tools; personal electronic equipment; and industrial robots etc.

"High Quality": Transportation equipment (automobiles, trains, ships, etc.); traffic control systems; anti-disaster systems; anti-crime systems; and safety equipment etc.

Renesas Electronics products are neither intended nor authorized for use in products or systems that may pose a direct threat to human life or bodily injury (artificial life support devices or systems, surgical implantations etc.), or may cause serious property damages (nuclear reactor control systems, military equipment etc.). You must check the quality grade of each Renesas Electronics product before using it in a particular application. You may not use any Renesas Electronics product for any application for which it is not intended. Renesas Electronics shall not be in any way liable for any damages or losse incurred by you or third parties arising from the use of any Renesas Electronics product for which the product is not intended by Renesas Electronics

- 6. You should use the Renesas Electronics products described in this document within the range specified by Renesas Electronics, especially with respect to the maximum rating, operating supply voltage range, movement power voltage range, heat radiation characteristics, installation and other product characteristics. Renesas Electronics shall have no liability for malfunctions or damages arising out of the ise of Renesas Electronics products beyond such specified ranges.
- 7. Although Renesas Electronics endeavors to improve the quality and reliability of its products, semiconductor products have specific characteristics such as the occurrence of failure at a certain rate and malfunctions under certain use conditions. Further, Renesas Electronics products are not subject to radiation resistance design. Please be sure to implement safety measures to guard them against the possibility of physical injury, and injury or damage caused by fire in the event of the failure of a Renesas Electronics product, such as safety design for hardware and software including but not limited to redundancy, fire control and malfunction prevention, appropriate treatment for aging degradation or any other appropriate measures. Because the evaluation of microcomputer software alone is very difficult, please evaluate the safety of the final products or systems manufactured by you.
- 8. Please contact a Renesas Electronics sales office for details as to environmental matters such as the environmental compatibility of each Renesas Electronics product. Please use Renesas Electronics products in compliance with all applicable laws and regulations that regulate the inclusion or use of controlled substances, including without limitation, the EU RoHS Directive. Renesas Electronics assumes no liability for damages or losses occurring as a result of your noncompliance with applicable laws and regulations.
- 9. Renesas Electronics products and technology may not be used for or incorporated into any products or systems whose manufacture, use, or sale is prohibited under any applicable domestic or foreign laws or regulations. You should not use Renesas Electronics products or technology described in this document for any purpose relating to military applications or use by the military, including but not limited to the development of weapons of mass destruction. When exporting the Renesas Electronics products or technology described in this document, you should comply with the applicable export control laws and regulations and follow the procedures required by such laws and regulations
- 10. It is the responsibility of the buyer or distributor of Renesas Electronics products, who distributes, disposes of, or otherwise places the product with a third party, to notify such third party in advance of the contents and conditions set forth in this document, Renesas Electronics assumes no responsibility for any losses incurred by you or third parties as a result of unauthorized use of Renesas Electronics products.
- 11. This document may not be reproduced or duplicated in any form, in whole or in part, without prior written consent of Renesas Electronics
- 12. Please contact a Renesas Electronics sales office if you have any questions regarding the information contained in this document or Renesas Electronics products, or if you have any other inquiries. (Note 1) "Renesas Electronics" as used in this document means Renesas Electronics Corporation and also includes its majority-owned subsidiaries
- (Note 2) "Renesas Electronics product(s)" means any product developed or manufactured by or for Renesas Electronics



#### **SALES OFFICES**

#### Renesas Electronics Corporation

http://www.renesas.com

Refer to "http://www.renesas.com/" for the latest and detailed information

Renesas Electronics America Inc. 2801 Scott Boulevard Santa Clara, CA 95050-2549, U.S.A. Tel: +1-408-588-6000, Fax: +1-408-588-6130

Renesas Electronics Canada Limited 1101 Nicholson Road, Newmarket, Ontario L3Y 9C3, Canada Tel: +1-905-898-5441, Fax: +1-905-898-3220

Renesas Electronics Europe Limited Dukes Meadow, Millboard Road, Bourne End, Buckinghamshire, SL8 5FH, U.K Tel: +44-1628-585-100, Fax: +44-1628-585-900

Renesas Electronics Europe GmbH

Arcadiastrasse 10, 40472 Düsseldorf, Germany Tel: +49-211-6503-0, Fax: +49-211-6503-1327

Renesas Electronics (China) Co., Ltd. Room 1709, Quantum Plaza, No.27 ZhiChunLu Haidian District, Beijing 100191, P.R.China Tei: +86-10-2035-1155, Fax: +86-10-8235-7679

Renesas Electronics (Shanghai) Co., Ltd.
Unit 301, Tower A, Central Towers, 555 Langao Road, Putuo District, Shanghai, P. R. China 200333
Tel: +86-21-2226-0888, Fax: +86-21-2226-0999

Renesas Electronics Hong Kong Limited
Unit 1601-1613, 161F., Tower 2, Grand Century Place, 193 Prince Edward Road West, Mongkok, Kowloon, Hong Kong
Tel: +852-2856-5688, Fax: +852 2886-9022/9044

Renesas Electronics Taiwan Co., Ltd. 13F, No. 363, Fu Shing North Road, Taipei 105-Tel: +886-2-8175-9600, Fax: +886 2-8175-9670 . ipei 10543, Taiwan

Renesas Electronics Singapore Pte. Ltd. 80 Bendemeer Road, Unit #06-02 Hyflux Innovation Centre, Singapore 339949 Tel: +65-6213-0200, Fax: +65-6213-0300

Renesas Electronics Malaysia Sdn.Bhd.
Unit 906, Block B, Menara Amcorp, Amcorp Trade Centre, No. 18, Jln Persiaran Barat, 46050 Petaling Jaya, Selangor Darul Ehsan, Malaysia
Tel: +60-3-7955-9390, Fax: +60-3-7955-9510

Renesas Electronics Korea Co., Ltd. 12F., 234 Teheran-ro, Gangnam-Ku, Seoul, 135-920, Korea Tel: +82-2-558-3737, Fax: +82-2-558-5141

© 2014 Renesas Electronics Corporation. All rights reserved.